

ABSTRACT

A semiconductor layer protruding beside a source line is removed in order to increase aperture ratio, decrease resistance of the source line and prevent source-common capacitance from increasing. When a part of a passivation film is removed to form a contact hole, the passivation film on the source line, the passivation film beside the source line and a gate insulating layer beside the source line are simultaneously removed. A portion protruding beside the source line is removed from thus exposed semiconductor layer using a resist pattern for removing the part of the passivation film and/or the source line as a mask.

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